

Data Sheet September 13, 2004 FN3137.5

CMOS Analog Multiplexers

The DG508A is a CMOS Monolithic 8-Channel Analog Multiplexer, which can also be used as a demultiplexer. An enable input is provided. When the enable input is high, a channel is selected by the address inputs, and when low, all channels are off.

A channel in the ON state conducts current equally well in both directions. In the OFF state each channel blocks voltages up to the supply rails. The address inputs and the enable input are TTL and CMOS compatible over the full specified operating temperature range.

The DG508A is pinout compatible with the industry standard devices.

Features

- · Low Power Consumption
- TTL and CMOS-Compatible Address and Enable Inputs
- · 44V Maximum Power Supply Rating
- · High Latch-Up Immunity
- · Break-Before-Make Switching
- · Alternate Source
- · Pb-free Available

Applications

- · Data Acquisition Systems
- · Communication Systems
- Signal Multiplexing/Demultiplexing
- · Audio Signal Multiplexing

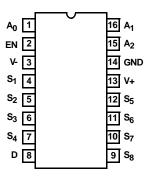
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. DWG.#
DG508AAK	-55 to 125	16 Ld CERDIP	F16.3
DG508ABK	-25 to 85	16 Ld CERDIP	F16.3
DG508ACJ	0 to 70	16 Ld PDIP	E16.3
DG508ACJZ (See Note)	0 to 70	16 Ld PDIP (Pb-free)	E16.3

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which is compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020C.

Pinout

DG508A (PDIP, CERDIP) TOP VIEW



Truth Table

DG508A

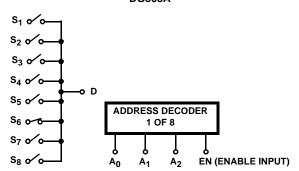
A ₂	A ₁	A ₀	EN	ON SWITCH
Х	Х	Х	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

A₀, A₁, A₂, EN

 $Logic "1" = V_{AH} \geq 2.4V, \ Logic "0" = V_{AL} \leq 0.8V$

Functional Diagram

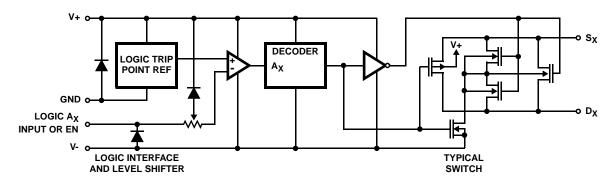
DG508A



3 Line Binary Address Inputs (1 0 1) and EN = 1

Above example shows channel 6 turned ON.

Schematic Diagram



Absolute Maximum Ratings

V+ to V	44V
V- to Ground	25V
Digital Inputs, V _S , V _D (Note 1)(V2V) To (V++	-2V)
Continuous Current, (Any Terminal Except S or D) 30)mÁ
Continuous Current, (S or D))mA
Peak Current, S or D (Pulsed 1ms, 10% Duty Cycle Max) 40)mA

Operating Conditions

Temperature Range	
"A" Suffix	55°C to 125°C
"B" Suffix	25°C to 85°C
"C" Suffix	0°C to 70°C

Thermal Information

Thermal Resistance (Typical, Note 2)	θ_{JA} (oC/W)	θ_{JC} (oC/W)
16 Ld CERDIP Package	75	20
16 Ld PDIP Package	90	N/A
Maximum Junction Temperature		
CERDIP Package		175°C
PDIP Package		150 ^o C
Maximum Storage Temperature		
"A" and "B" Suffix	6	5°C to 150°C
"C" Suffix	6	5 ⁰ C to 125 ⁰ C
Maximum Lead Temperature (Soldering 1	0s)	300°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- 1. Signals on S_X , D, E_N , or A_X exceeding V+ or V- are clamped by internal diodes. Limit diode current to maximum current ratings.
- 2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications $T_A = 25^{\circ}C$, $V_{+} = +15V$, $V_{-} = -15V$, GND = 0V, $V_{EN} = 2.4V$, Unless Otherwise Specified

			•	"A" SUFFIX			"B" AND "C" SUFFIX		
PARAMETER	TEST	CONDITIONS	(NOTE 4)	(NOTE 3)	(NOTE 4) MAX	(NOTE 4)	(NOTE 3)	(NOTE 4) MAX	UNITS
DYNAMIC CHARACTERIS	TICS			Į.	Į.	J.	Į.		
Switching Time of Multiplexer, t _{TRANSITION}	See Figure 1		-	0.6	1	-	0.6	-	μS
Break-Before-Make Interval, t _{OPEN}	See Figure 3		-	0.2	-	-	0.2	-	μS
Enable Turn-ON Time, [†] ON(EN)	See Figure 2		-	1	1.5	-	1	-	μS
Enable Turn-OFF Time, ^t OFF(EN)	See Figure 2		-	0.4	1.0	-	0.4	-	μS
OFF Isolation, OIRR	$V_{EN} = 0V, R_{L} = 0$ $V_{S} = 7V_{RMS}, f = 0$	-	68	-	-	68	-	dB	
Source OFF Capacitance, C _{S(OFF)}	$V_S = 0V$, $V_{EN} = 0$	-	5	-	-	5	ı	pF	
Drain OFF Capacitance, C _{D(OFF)}	$V_D = 0V$, $V_{EN} = 0$	-	25	-	-	25	-	pF	
Charge Injection, Q	See Figure 4		-	4	-	-	4	-	рС
DIGITAL INPUT CHARACT	ERISTICS								
Address Input Current,	V _A = 2.4V		-10	-0.002	-	-10	-0.002	-	μΑ
Input Voltage High, I _{AH}	V _A = 15V		-	0.006	10	-	0.006	10	μА
Address Input Current Input	V _{EN} = 2.4V	$V_A = 0V$	-10	-0.002	-	-10	-0.002	1	μА
Voltage Low, I _{AL}	V _{EN} = 0V		-10	-0.002	-	-10	-0.0002	-	μА
ANALOG SWITCH CHARA	CTERISTICS								1
Analog Signal Range, VANALOG	(Note 7)		-15	-	+15	-15	-	+15	V
Drain-Source ON	Sequence Each	$I_S = -200 \mu A, V_D = +10 V$	-	270	400	-	270	450	Ω
$V_{AL} = 0$	Switch ON $V_{AL} = 0.8V$, $V_{AH} = 2.4V$	$I_S = -200 \mu A, V_D = -10 V$	-	230	400	-	230	450	Ω
r _{DS(ON)} Matching Between Channels	$V_{AH} = 2.4V$ $-10V \le V_S \le +10V$ $\Delta r_{DS(ON)} = \frac{r_{DS(ON)MAX} - r_{DS(ON)MIN}}{r_{DS(ON)AVG}}$		-	6	-	-	6	-	%

Electrical Specifications $T_A = 25^{\circ}C$, $V_{+} = +15V$, $V_{-} = -15V$, GND = 0V, $V_{EN} = 2.4V$, Unless Otherwise Specified (Continued)

			"A" SUFFIX		"B" AND "C" SUFFIX				
PARAMETER	TEST CONDITIONS		(NOTE 4) MIN	(NOTE 3) TYP	(NOTE 4) MAX	(NOTE 4) MIN	(NOTE 3) TYP	(NOTE 4) MAX	UNITS
Source OFF Leakage	V _{EN} = 0V	$V_S = +10V, V_D = -10V$	-1	0.002	1	-5	0.002	5	nA
Current, I _{S(OFF)}		$V_S = -10V, V_D = +10V$	-1	-0.005	1	-5	-0.005	5	nA
Drain OFF Leakage	V _{EN} = 0V	$V_S = -10V, V_D = +10V$	-	0.01	10	-	0.01	20	nA
Current, I _{D(OFF)}		$V_S = +10V, V_D = -10V$	-10	-0.015	-	-20	-0.015	-	nA
Drain ON Leakage Current,	(Note 6)	$V_D = V_{S(ALL)} = +10V$	-	0.015	10	-	0.015	20	nA
$I_{D(ON)}$ Sequence Each Switch ON $V_{AL} = 0.8V$, $V_{\Delta H} = 2.4V$	Switch ON	$V_D = V_{S(ALL)} = -10V$	-10	-0.03	-	-20	-0.03	-	nA
POWER SUPPLY CHARACTERISTICS									
Positive Supply Current, I+	V _{EN} = 5.0V (Ena		-	1.3	2.4	-	1.3	2.4	mA
Negative Supply Current, I-	V _{EN} = 0V (Stand	$(by), V_A = 0V$	-1.5	-0.7	-	-1.5	-0.7	-	mA

Electrical Specifications

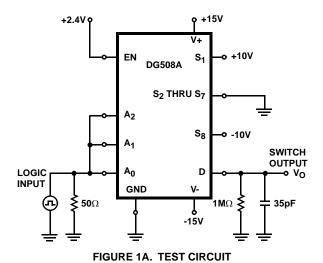
 T_A = Over Operating Temperature Range, V+ = +15V, V- = -15V, GND = 0V, V_{EN} = 2.4V, Unless Otherwise Specified

			1	(
PARAMETER	TEST CONDIT	TIONS	MIN	(NOTE 3)	MAX	UNITS
DIGITAL INPUT CHARACTERISTICS			'			
Address Input Current, Input Voltage High, I _{AH}	V _A = 2.4V		-30	-	-	μА
	V _A = 15V		-	-	30	μΑ
Address Input Current Input Voltage	V _{EN} = 2.4V	$V_A = 0V$	-30	-	-	μА
Low, I _{AL}	V _{EN} = 0V		-30	-	-	μА
ANALOG SWITCH CHARACTERISTIC	s			*		
Analog Signal Range, V _{ANALOG}	(Note 7)		-15	-	+15	V
Drain-Source ON Resistance, r _{DS(ON)}	Sequence Each Switch ON V _{AL} = 0.8V, V _{AH} = 2.4V	$I_S = -200 \mu A, V_D = +10 V$	-	-	500	Ω
		$I_S = -200 \mu A, V_D = -10 V$	-	-	500	Ω
Source OFF Leakage Current, I _{S(OFF)}	V _{EN} = 0V	$V_S = +10V, V_D = -10V$	-	-	50	nA
		V _S = -10V, V _D = +10V	-50	-	-	nA
Drain OFF Leakage Current, I _{D(OFF)}	V _{EN} = 0V	$V_S = -10V, V_D = +10V$	-	-	200	nA
		V _S = +10V, V _D = -10V	-200	-	-	nA
Drain ON Leakage Current, I _{D(ON)}	(Note 6) Sequence Each Switch ON	$V_D = V_{S(ALL)} = +10V$	-	-	200	nA
	$V_{AL} = 0.8V, V_{AH} = 2.4V$	$V_D = V_{S(ALL)} = -10V$	-200	-	-	nA
POWER SUPPLY CHARACTERISTICS	3		·			
Positive Supply Current, I+		$V_{EN} = 5.0V, V_A = 0V$	-3.2	-	4.5	mA
Negative Supply Current, I-			-3.2	-	4.5	mA
Positive Standby Supply Current, I+		$V_{EN} = 0V$, $V_A = 0V$	-3.2	-	4.5	mA
Negative Standby Supply Current, I-		1	-3.2	-	4.5	mA

NOTES:

- 3. Typical values are for design aid only, not guaranteed and not subject to production testing.
- 4. The algebraic convention whereby the most negative value is a minimum, and the most positive value is a maximum, is used in this data sheet.
- 5. Off isolation = $20Log |V_S|/|V_D|$, where V_S = input to Off switch, and V_D = output due to V_S .
- 6. $I_{D(ON)}$ is leakage from driver into "ON" switch.
- 7. Parameter not tested. Parameter guaranteed by design or characterization.

Test Circuits and Waveforms



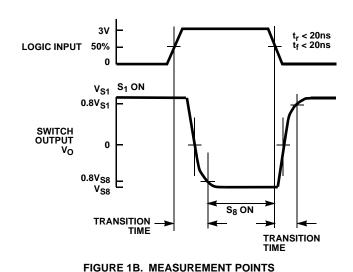
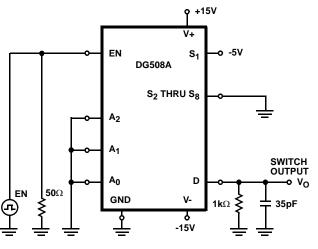


FIGURE 1. SWITCHING TIME



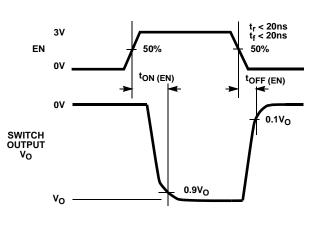
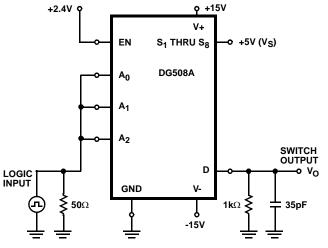


FIGURE 2A. TEST CIRCUIT

FIGURE 2B. MEASUREMENT POINTS

FIGURE 2. ENABLE TIMES



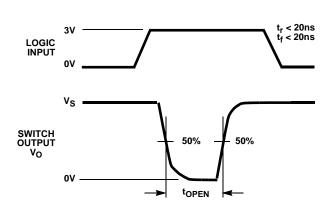
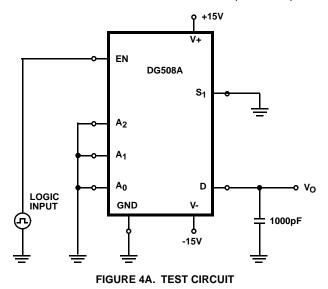


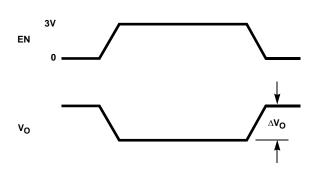
FIGURE 3A. TEST CIRCUIT

FIGURE 3B. MEASUREMENT POINTS

FIGURE 3. BREAK-BEFORE-MAKE INTERVAL

Test Circuits and Waveforms (Continued)





 $\Delta V_{\mbox{\scriptsize O}}$ is the measured voltage error due to charge injection. The charge transfer error in Coulombs is Q = C_L x $\Delta V_{\mbox{\scriptsize O}}.$

FIGURE 4B. CHARGE INJECTION WAVEFORMS

FIGURE 4. CHARGE INJECTION

Typical Performance Curves

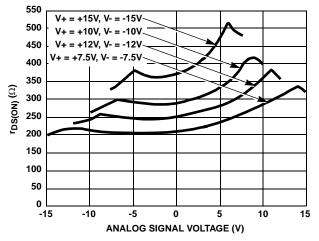


FIGURE 5. $r_{DS(ON)}$ vs analog signal voltage vs supply voltage

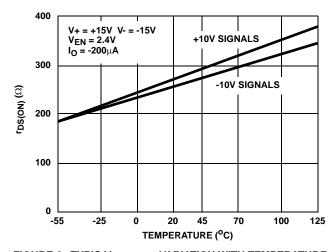


FIGURE 6. TYPICAL $r_{\text{DS(ON)}}$ VARIATION WITH TEMPERATURE

Die Characteristics

DIE DIMENSIONS:

 $3100 \mu m \ x \ 2083 \mu m$

METALLIZATION:

Type: Al

Thickness: 10kÅ ±1kÅ

PASSIVATION:

Type: PSG/Nitride

Thickness: PSG: 7kÅ ±1.4kÅ

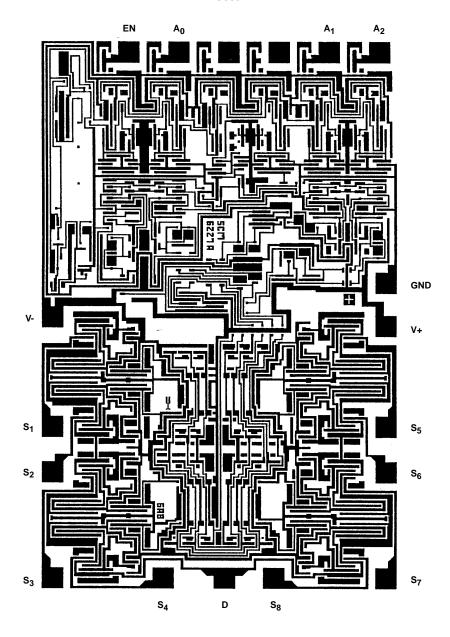
Nitride: 8kÅ ±1.2kÅ

WORST CASE CURRENT DENSITY:

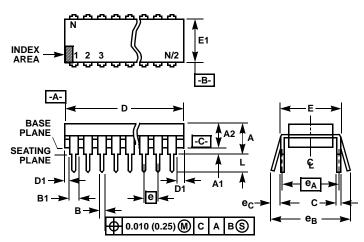
9.1 x 10⁴ A/cm²

Metallization Mask Layout

DG508A



Dual-In-Line Plastic Packages (PDIP)



NOTES:

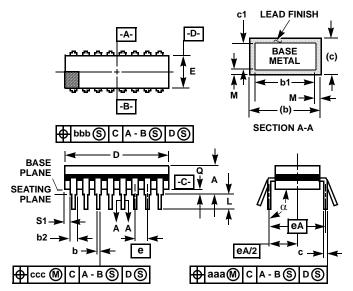
- Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- 3. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
- Dimensions A, A1 and L are measured with the package seated in JE-DEC seating plane gauge GS-3.
- D, D1, and E1 dimensions do not include mold flash or protrusions.
 Mold flash or protrusions shall not exceed 0.010 inch (0.25mm).
- E and eA are measured with the leads constrained to be perpendicular to datum -C-.
- 7. e_B and e_C are measured at the lead tips with the leads unconstrained. e_C must be zero or greater.
- 8. B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch (0.25mm).
- 9. N is the maximum number of terminal positions.
- Corner leads (1, N, N/2 and N/2 + 1) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030 - 0.045 inch (0.76 - 1.14mm).

E16.3 (JEDEC MS-001-BB ISSUE D)
16 LEAD DUAL-IN-LINE PLASTIC PACKAGE

TO EEAD DOAE IN LINE I EAGING I AGNAGE								
	INC	HES	MILLIM	ETERS				
SYMBOL	MIN	MAX	MIN	MAX	NOTES			
Α	-	0.210	-	5.33	4			
A1	0.015	-	0.39	-	4			
A2	0.115	0.195	2.93	4.95	-			
В	0.014	0.022	0.356	0.558	-			
B1	0.045	0.070	1.15	1.77	8, 10			
С	0.008	0.014	0.204	0.355	-			
D	0.735	0.775	18.66	19.68	5			
D1	0.005	-	0.13	-	5			
Е	0.300	0.325	7.62	8.25	6			
E1	0.240	0.280	6.10	7.11	5			
е	0.100	BSC	2.54	BSC	-			
e _A	0.300	BSC	7.62 BSC		6			
e _B	-	0.430	-	10.92	7			
L	0.115	0.150	2.93	3.81	4			
N	16		1	9				

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Ceramic Dual-In-Line Frit Seal Packages (CERDIP)



NOTES:

- Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
- The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
- Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
- Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
- 5. This dimension allows for off-center lid, meniscus, and glass
- 6. Dimension Q shall be measured from the seating plane to the base plane.
- 7. Measure dimension S1 at all four corners.
- 8. N is the maximum number of terminal positions.
- 9. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 10. Controlling dimension: INCH.

F16.3 MIL-STD-1835 GDIP1-T16 (D-2, CONFIGURATION A)
16 LEAD CERAMIC DUAL-IN-LINE FRIT SEAL PACKAGE

	INC	HES	MILLIM		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	-	0.200	-	5.08	-
b	0.014	0.026	0.36	0.66	2
b1	0.014	0.023	0.36	0.58	3
b2	0.045	0.065	1.14	1.65	-
b3	0.023	0.045	0.58	1.14	4
С	0.008	0.018	0.20	0.46	2
c1	0.008	0.015	0.20	0.38	3
D	-	0.840	-	21.34	5
E	0.220	0.310	5.59	7.87	5
е	0.100	BSC	2.54	-	
eA	0.300	BSC	7.62 BSC		-
eA/2	0.150	BSC	3.81	BSC	-
L	0.125	0.200	3.18	5.08	-
Q	0.015	0.060	0.38	1.52	6
S1	0.005	-	0.13	-	7
α	90°	105 ⁰	90°	105 ⁰	-
aaa	-	0.015	-	0.38	-
bbb	-	0.030	-	0.76	-
ccc	-	0.010	-	0.25	-
М	-	0.0015	-	0.038	2, 3
N	1	6	1	8	

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